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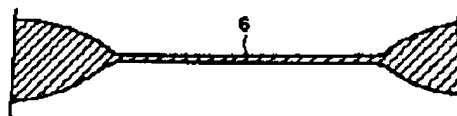
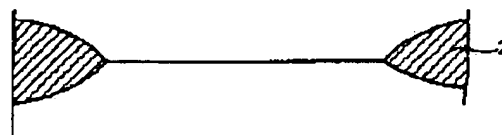
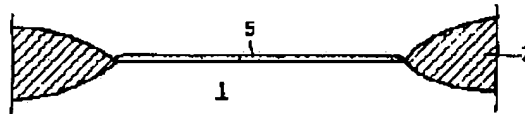
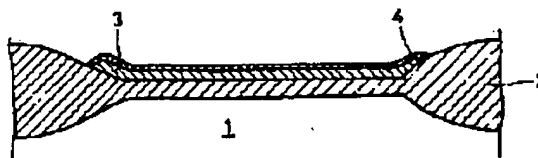
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**(54) MANUFACTURE OF  
SEMICONDUCTOR DEVICE**

(57) Abstract:

**PURPOSE:** To perform etching of an Si oxide film and an Si nitride film by a dry method without damaging a substrate by etching the Si oxide film and the Si nitride film by exposing these to F-group gas containing specific atoms, and mixed gas of aforesaid F-group gas and H<sub>2</sub>O, H<sub>2</sub>.

**CONSTITUTION:** Etching of an Si oxide film 3 and an Si nitride film 4 is performed by exposing these to F-group gas containing F-atoms of HF, F<sub>2</sub>, XeF<sub>2</sub> and to mixed gas of aforesaid F-group gas and H<sub>2</sub>O, H<sub>2</sub>. Etching of a nitride film, an oxide film is performed according to an etching property, thickness of semiconductor constitution materials such as single Si, polySi, a nitride film, an oxide film and the kinds of F-group gas, and the materials around them are made to remain. During an etching process, ultraviolet light is directly applied to F-group gas or a substrate 1. After the etching process, annealing is performed. After etching or annealing processes, again a film 6 is formed. Directly before finishing the etching process, F-group gas is changed to F-group gas having low etching speed of the semiconductor substrate.



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